Single 2-Input OR Gate

The NL17SH32 is an advanced high speed CMOS 2-input OR gate fabricated with silicon gate CMOS technology.

The internal circuit is composed of multiple stages, including a buffer output which provides high noise immunity and stable output.

The NL17SH32 input structure provides protection when voltages up to 7 V are applied, regardless of the supply voltage. This allows the NL17SH32 to be used to interface 5 V circuits to 3 V circuits.

Features

- High Speed: $t_{PD} = 3.7 \text{ ns}$ (Typ) at $V_{CC} = 5 \text{ V}$
- Low Power Dissipation: $I_{CC} = 1 \mu A \text{ (Max)}$ at $T_A = 25^{\circ}\text{C}$
- Power Down Protection Provided on Inputs
- Balanced Propagation Delays
- Pin and Function Compatible with Other Standard Logic Families
- These are Pb-Free Devices

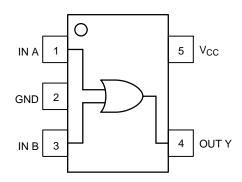


Figure 1. Pinout (Top View)



Figure 2. Logic Symbol



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MARKING DIAGRAM



SOT-953 CASE 527AE



F = Specific Device Code

M = Month Code

PIN ASSIGNMENT					
1	IN A				
2	GND				
3	IN B				
4	OUT Y				
5	V _{CC}				

FUNCTION TABLE

Inp	uts	Output
Α	В	Y
L	L	L
L	Н	Н
Н	L	Н
Н	Н	Н

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 4 of this data sheet.

NL17SH32

MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V _{CC}	DC Supply Voltage	-0.5 to +7.0	V
V _{IN}	DC Input Voltage	-0.5 to +7.0	V
V _{OUT}	DC Output Voltage	-0.5 to V _{CC} +0.5	V
I _{IK}	DC Input Diode Current	-20	mA
I _{OK}	DC Output Diode Current	±20	mA
I _{OUT}	DC Output Sink Current	±25	mA
I _{CC}	DC Supply Current per Supply Pin	50	mA
T _{STG}	Storage Temperature Range	-65 to +150	°C
T _L	Lead Temperature, 1 mm from Case for 10 Seconds	260	°C
TJ	Junction Temperature Under Bias	+150	°C
P _D	Power Dissipation in Still Air	50	mW
MSL	Moisture Sensitivity	Level 1	
F _R	Flammability Rating Oxygen Index: 28 to 34	UL 94 V-0 @ 0.125 in	
I _{LATCHUP}	Latchup Performance Above V _{CC} and Below GND at 125°C (Note 1)	±100	mA

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

RECOMMENDED OPERATING CONDITIONS

Symbol	Characteristics			Max	Unit
V _{CC}	DC Supply Voltage	2.	0	5.5	V
V _{IN}	DC Input Voltage	0.	0.0	5.5	V
V _{OUT}	DC Output Voltage	0.	0.0	V _{CC}	V
T _A	Operating Temperature Range	-5	55	+125	°C
t _r , t _f	Input Rise and Fall Time $ \begin{array}{c} V_{CC} = 0 \\ V_{CC} = 0 \end{array} $		0 0	100 20	ns/V

Device Junction Temperature versus Time to 0.1% Bond Failures

Junction Temperature °C	Time, Hours	Time, Years
80	1,032,200	117.8
90	419,300	47.9
100	178,700	20.4
110	79,600	9.4
120	37,000	4.2
130	17,800	2.0
140	8,900	1.0

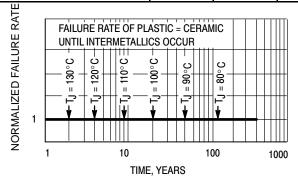


Figure 3. Failure Rate vs. Time Junction Temperature

^{1.} Tested to EIA/JESD78.

NL17SH32

DC ELECTRICAL CHARACTERISTICS

			v _{cc}	Т	_A = 25°	С	T _A ≤	85°C	−55°C t	o 125°C	
Symbol	Parameter	Test Conditions	(V)	Min	Тур	Max	Min	Max	Min	Max	Unit
V _{IH}	Minimum High-Level Input Voltage		2.0 3.0 4.5 5.5	1.5 2.1 3.15 3.85			1.5 2.1 3.15 3.85		1.5 2.1 3.15 3.85		V
V _{IL}	Maximum Low-Level Input Voltage		2.0 3.0 4.5 5.5			0.5 0.9 1.35 1.65		0.5 0.9 1.35 1.65		0.5 0.9 1.35 1.65	V
V _{OH}	Minimum High-Level Output Voltage V _{IN} = V _{IH} or V _{IL}	$V_{IN} = V_{IH} \text{ or } V_{IL}$ $I_{OH} = -50 \mu\text{A}$	2.0 3.0 4.5	1.9 2.9 4.4	2.0 3.0 4.5		1.9 2.9 4.4		1.9 2.9 4.4		V
		V_{IN} = V_{IH} or V_{IL} I_{OH} = -4 mA I_{OH} = -8 mA	3.0 4.5	2.58 3.94			2.48 3.80		2.34 3.66		
V _{OL}	Maximum Low-Level Output Voltage V _{IN} = V _{IH} or V _{IL}	$V_{IN} = V_{IH} \text{ or } V_{IL}$ $I_{OL} = 50 \mu\text{A}$	2.0 3.0 4.5		0.0 0.0 0.0	0.1 0.1 0.1		0.1 0.1 0.1		0.1 0.1 0.1	V
		$V_{IN} = V_{IH}$ or V_{IL} $I_{OL} = 4$ mA $I_{OL} = 8$ mA	3.0 4.5			0.36 0.36		0.44 0.44		0.52 0.52	
I _{IN}	Maximum Input Leakage Current	V _{IN} = 5.5 V or GND	0 to 5.5			±0.1		±1.0		±1.0	μΑ
I _{CC}	Maximum Quiescent Supply Current	$V_{IN} = V_{CC}$ or GND	5.5			1.0		10		40	μΑ

AC ELECTRICAL CHARACTERISTICS C_{load} = 50 pF, Input t_r = t_f = 3.0 ns

				T _A = 25°C		$T_A = 25^{\circ}C$ $T_A \le 85^{\circ}C$		85°C	-55 ≤ T _A	≤ 125°C	
Symbol	Parameter	Test Cond	itions	Min	Тур	Max	Min	Max	Min	Max	Unit
t _{PLH} , t _{PHL}	Maximum Propagation Delay, Input A or B to Y	$V_{CC} = 3.3 \pm 0.3 \text{ V}$	C _L = 15 pF C _L = 50 pF		4.8 6.1	7.9 11.4		9.5 13.0		11.5 15.5	ns
	input A of B to 1	$V_{CC} = 5.0 \pm 0.5 \text{ V}$	$C_L = 15 pF$ $C_L = 50 pF$		3.7 4.4	5.5 7.5		6.5 8.5		8.0 10.0	
C _{IN}	Maximum Input Capacitance				5.5	10		10		10	pF

		Typical @ 25°C, V _{CC} = 5.0 V	
C_{PD}	Power Dissipation Capacitance (Note 2)	11	pF

^{2.} C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load. Average operating current can be obtained by the equation: I_{CC(OPR)} = C_{PD} • V_{CC} • f_{in} + I_{CC}. C_{PD} is used to determine the no–load dynamic power consumption; P_D = C_{PD} • V_{CC}² • f_{in} + I_{CC} • V_{CC}.

NL17SH32

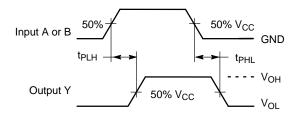
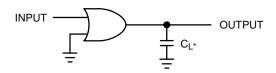


Figure 4. Switching Waveforms



*Includes all probe and jig capacitance. A 1–MHz square input wave is recommended for propagation delay tests.

Figure 5. Test Circuit

ORDERING INFORMATION

Device	Package	Shipping [†]
NL17SH32P5T5G	SOT-953 (Pb-Free)	8000 / Tape & Reel

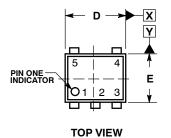
[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

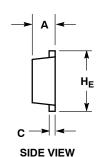


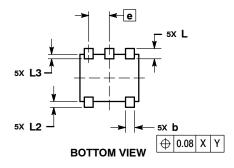
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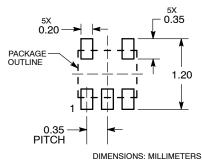








SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

NOTES:

- DIMENSIONING AND TOLERANCING PER ASME
- Y14.5M, 1994.
 2. CONTROLLING DIMENSION: MILLIMETERS
- MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE
- MINIMUM THICKNESS OF THE BASE MATERIAL.
 DIMENSIONS D AND E DO NOT INCLUDE MOLD
 FLASH, PROTRUSIONS, OR GATE BURRS.

	MILLIMETERS							
DIM	MIN NOM MAX							
Α	0.34	0.37	0.40					
b	0.10	0.15	0.20					
С	0.07	0.12	0.17					
D	0.95 1.00		1.05					
E	0.75	0.80	0.85					
е		0.35 BS	С					
HE	0.95	0.95 1.00						
L	(0.175 RE	F					
L2	0.05	0.10	0.15					
L3			0.15					

GENERIC MARKING DIAGRAM*



= Specific Device Code = Month Code

*This information is generic. Please refer to device data sheet for actual part marking.

Pb-Free indicator, "G" or microdot " ■", may or may not be present.

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